

ABSTRACT OF THE DISCLOSURE

In a display device including thin film transistors formed on an insulation substrate, the thin film transistor includes a semiconductor layer, a gate electrode and a gate insulation film which is interposed between the semiconductor layer and the gate electrode. The gate insulation film includes at least one layer of deposition film which is deposited by a deposition method, and the carbon concentration of the gate insulation film which is formed without interposing other deposition film deposited by a deposition method between the one deposition film and the semiconductor layer has the distribution in which the carbon concentration is smaller at a side close to the semiconductor layer than at a side remote from the semiconductor layer. Due to such a constitution, it is possible to obviate the elevation of a level of an interface of the insulation film with respect to a poly silicon layer and it is also possible to obviate an increase of fixed charges in the inside of the insulation film in the thin film transistor.